

MBR735 ~ MBR760

PRV : 35~60 Volts
Io : 7.5 Amperes

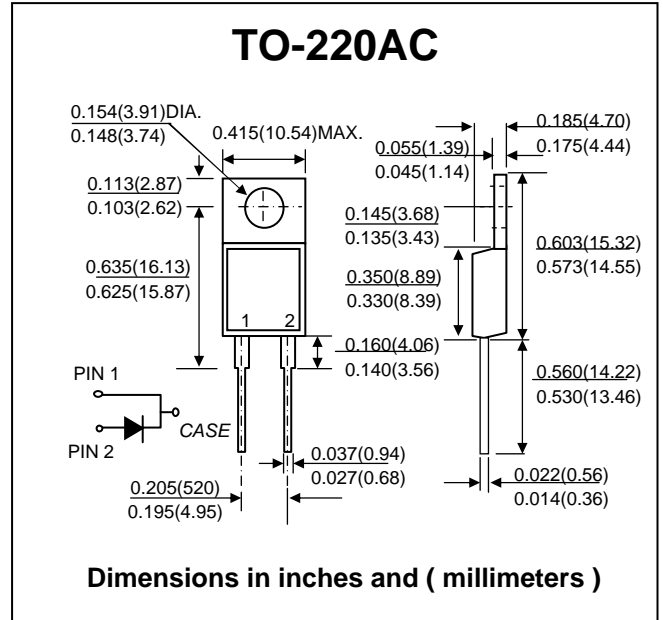
FEATURES :

- * Plastic package has Underwriters Laboratory Flammability Classifications 94V-0
- * Metal silicon junction, majority carrier conduction
- * Low power loss, high efficiency
- * Guardring for overvoltage protection
- * For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- * High temperature soldering : 250°C/10 seconds, 0.25" (6.35mm) from case
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : JEDEC TO-220AC molded plastic body
- * Terminals: Plated leads, solderable per MIL-STD-750 Method 2026
- * Polarity: As marked
- * Mounting Position: Any
- * Weight : 2.24 grams (Approximately)

SCHOTTKY BARRIER RECTIFIER DIODES



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T_c = 25 °C unless otherwise noted)

RATINGS	SYMBOL	MBR735	MBR745	MBR750	MBR760	UNIT
Maximum Reptitive Peak Reverse Voltage	V _{RRM}	35	45	50	60	V
Maximum Working Peak Reverse Voltage	V _{RWM}	35	45	50	60	V
Maximum DC Blocking Voltage	V _{DC}	35	45	50	60	V
Maximum Average Forward Rectified Current (See Fig. 1)	I _{F(AV)}	7.5				A
Peak Forward Surg Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	150				A
Maximum Instantaneous Forward Voltage (Note 1) at I _F = 7.5 A, T _C = 25 °C at I _F = 7.5 A, T _C = 125 °C	V _F	-		0.75		V
		0.57		0.65		
Maximum Reverse Current at Rate	I _R	0.1		0.5		mA
Peak Reverse Voltage	I _{R(H)}	15		50		
Typical Thermal Resistance	R _{θJC}	3.0				°C/W
Operating Junction Temperature Range	T _J	-65 to + 150				°C
Storage Temperature Range	T _{STG}	-65 to + 175				°C

Note :

(1) Pulse test : 300 μs pluse width, 1% duty cycle

RATING AND CHARACTERISTIC CURVES (MBR735 ~ MBR760)

FIG.1 - FORWARD CURRENT DERATING CURVE

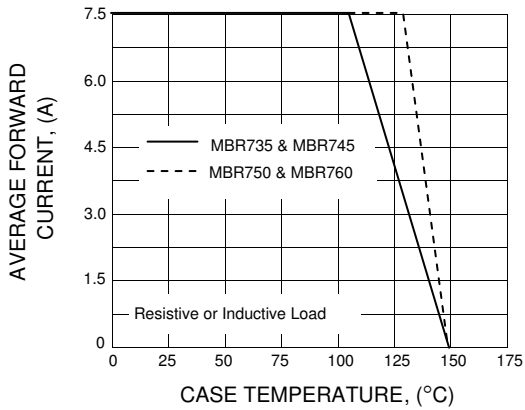


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

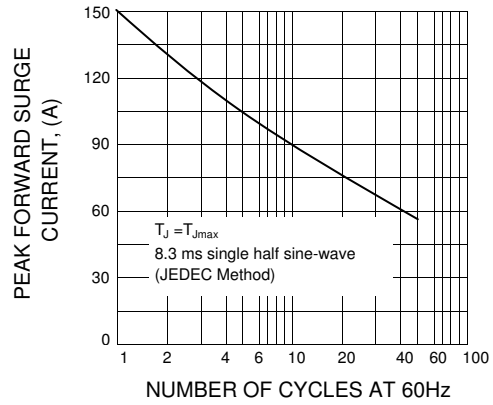


FIG.3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

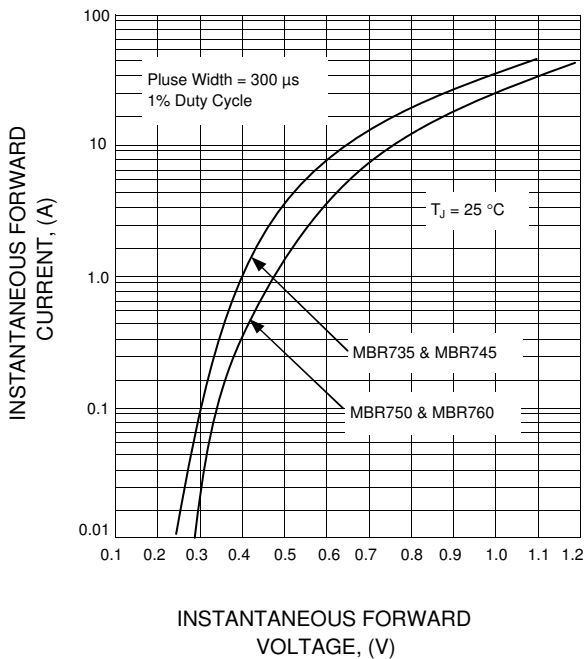


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

